

APPENDIX A**Paragraph [37] on page 11:**

[37] The gate oxide of the TFT device is made in the invention using substantially the same ISSG process described above (i.e., that described for SONOS devices) except that for TFT devices, the oxide is grown over polysilicon. Thus, the growth rates will be more than the growth rates described above for SONOS devices. Accordingly, lower process temperatures and/or shorter times will be required for TFT devices to obtain a similar oxide thickness as SONOS devices. In one aspect of the invention, the temperature for the ISSG process used to make the gate dielectric for TFT devices can range [form] from about 600 to about 900 degrees Celsius, preferably about 700 to about 850 degrees Celsius, and more preferably about 800 degrees Celsius.

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